

SPECIFICATION OF LED CHIP

C650-30E

[Red]

1) Commodity Type and Physical Characteristics.

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|----------------------|-------------------------------|----------------|
| 1. Material | InGaAlP | |
| 2. Electrode | Top Side P (anode)side | :Au Alloy/ Pad |
| | Bottom Side N (cathode)side | :Au Alloy |
| 3. Electrode Pattern | | Fig.1 |
| 4. Chip Size | | Fig.2 |
| 5. Chip Thickness | | Fig.2 |
| 6. Emission Area | | Fig.2 |

2) Electro-Optical Characteristics [Ta=25°C]

Parameters	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=20mA		1.8	2.2	V
Reverse Current	Ir	Vr=5V			10	uA
Brightness	Iv	If=20mA		120		mcd
Power Intensity	Po	If=20mA		3		mW
Peak Wavelength	λ_P	If=20mA	640	650	660	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		15		nm
RiseTime	tr	If=20mA				ns
FallTime	tf	If=20mA				ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

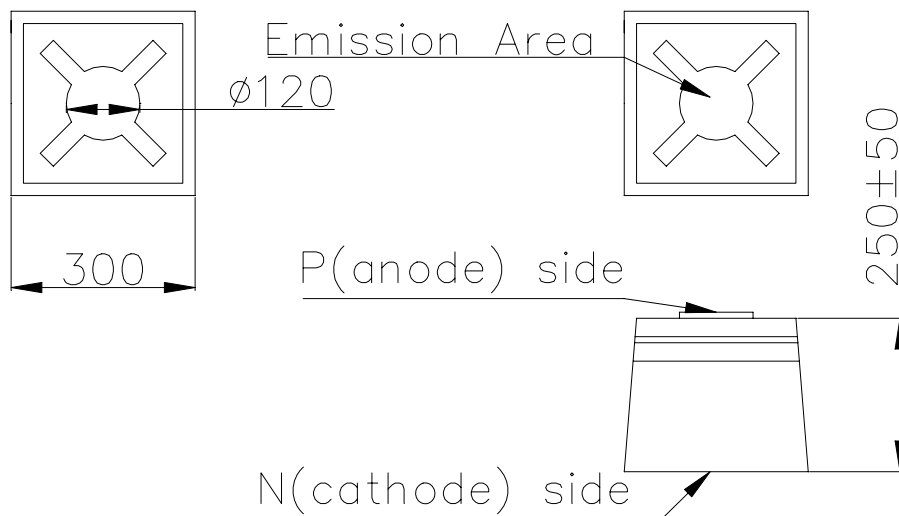


Fig.1 Electrode Pattern Fig.2 Chip size and Emission Area

Marubeni America Corporation

3945 Freedom Circle, Suite 1000, Santa Clara, CA 95054

408-330-0650 (Ext. 323), 408-330-0655 (Fax), sales@tech-led.com